

## FDD5680

### N-Channel, PowerTrench™ MOSFET

#### General Description

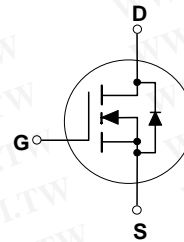
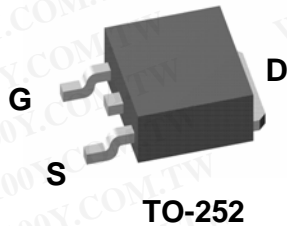
This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

#### Applications

- DC/DC converter
- Motor drives

#### Features

- 38 A, 60 V.  $R_{DS(on)} = 0.021 \Omega @ V_{GS} = 10 \text{ V}$   
 $R_{DS(on)} = 0.025 \Omega @ V_{GS} = 6 \text{ V}$ .
- Low gate charge (33nC typical).
- Fast switching speed.
- High performance trench technology for extremely low  $R_{DS(on)}$ .



#### Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage	60	V
V <sub>GSS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Maximum Drain Current - Continuous (Note 1) (Note 1a)	38 8.5	A
	Maximum Drain Current - Pulsed	100	
P <sub>D</sub>	Maximum Power Dissipation @ T <sub>C</sub> = 25°C (Note 1)	60	W
	T <sub>A</sub> = 25°C (Note 1a)	2.8	
	T <sub>A</sub> = 25°C (Note 1b)	1.3	
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

#### Thermal Characteristics

R <sub>θJC</sub>	Thermal Resistance, Junction-to- Case (Note 1)	2.1	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction-to- Ambient (Note 1b)	96	°C/W

#### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDD5680	FDD5680	13"	16mm	2500

### Electrical Characteristics

T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
--------	-----------	-----------------	-----	-----	-----	-------

#### Off Characteristics

W <sub>DSS</sub>	Single Pulse Drain-Source Avalanche Energy	V <sub>DD</sub> = 30 V, I <sub>D</sub> = 38 A			140	mJ
I <sub>AR</sub>	Maximum Drain-Source Avalanche Current				38	A
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	60			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		60		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 48 V, V <sub>GS</sub> = 0 V			1	μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 20V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -20 V, V <sub>DS</sub> = 0 V			-100	nA

#### On Characteristics (Note 2)

V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2	2.4	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		-6.4		mV/°C
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 8.5 A V <sub>GS</sub> = 10 V, I <sub>D</sub> = 8.5 A, T <sub>J</sub> = 125°C V <sub>GS</sub> = 6 V, I <sub>D</sub> = 7.5 A		0.017 0.028 0.019	0.021 0.042 0.025	Ω
I <sub>D(on)</sub>	On-State Drain Current	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 5 V	50			A
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 8.5 A		30		S

#### Dynamic Characteristics

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz		1835		pF
C <sub>oss</sub>	Output Capacitance			210		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			90		pF

#### Switching Characteristics (Note 2)

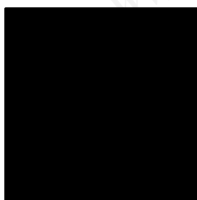
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 30 V, I <sub>D</sub> = 1 A, V <sub>GS</sub> = 10 V, R <sub>GEN</sub> = 6 Ω		15	27	ns
t <sub>r</sub>	Turn-On Rise Time			9	18	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			35	56	ns
t <sub>f</sub>	Turn-Off Fall Time			16	26	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 30 V, I <sub>D</sub> = 8.5 A, V <sub>GS</sub> = 10 V,		33	46	nC
Q <sub>gs</sub>	Gate-Source Charge			6.5		nC
Q <sub>gd</sub>	Gate-Drain Charge			7.5		nC

#### Drain-Source Diode Characteristics and Maximum Ratings

I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current			2.3		A
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 2.3 A (Note 2)		0.75	1.2	V

#### NOTES:

- R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the drain tab. R<sub>θJC</sub> is guaranteed by design while R<sub>θJA</sub> is determined by the user's board design.



■ a) R<sub>θJA</sub> = 45°C/W when mounted on a 1 in<sup>2</sup> pad of 2oz copper.

■ b) R<sub>θJA</sub> = 96°C/W when mounted on a 0.076 in<sup>2</sup> pad of 2oz copper.

Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

### Typical Characteristics

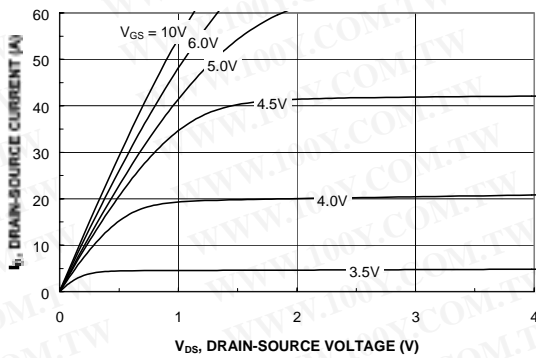


Figure 1. On-Region Characteristics.

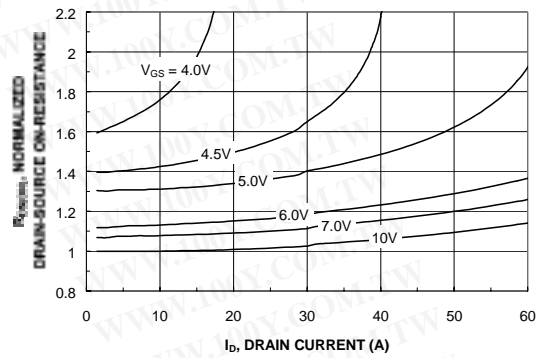


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

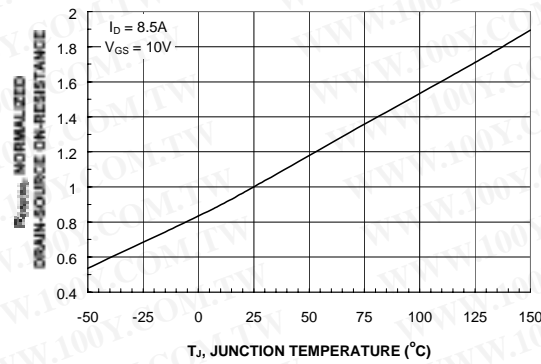


Figure 3. On-Resistance Variation with Temperature.

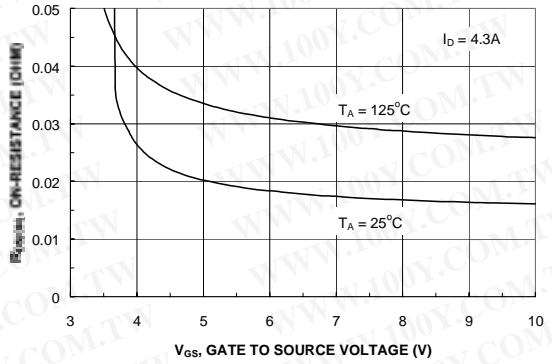


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

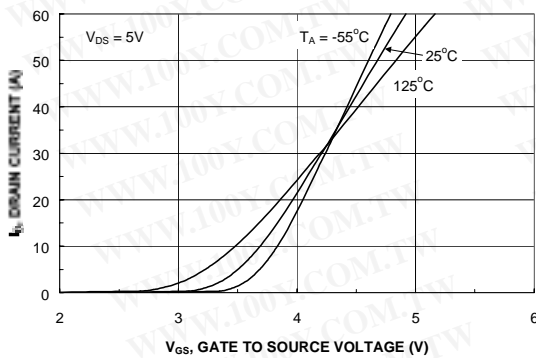


Figure 5. Transfer Characteristics.

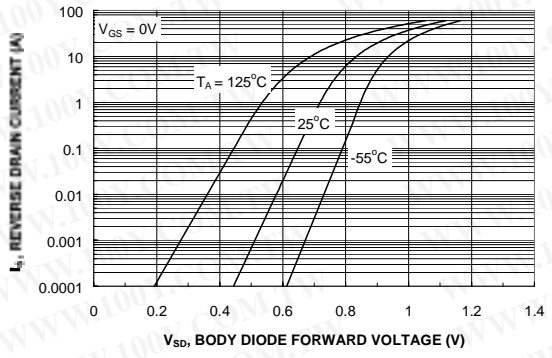


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)

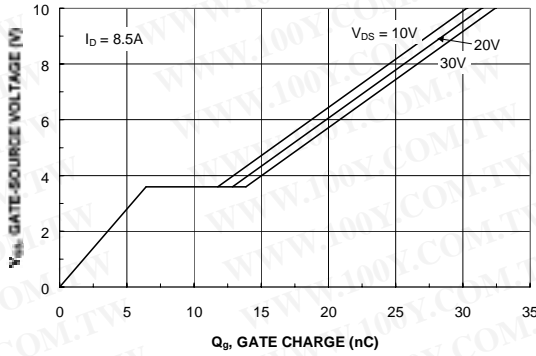


Figure 7. Gate-Charge Characteristics.

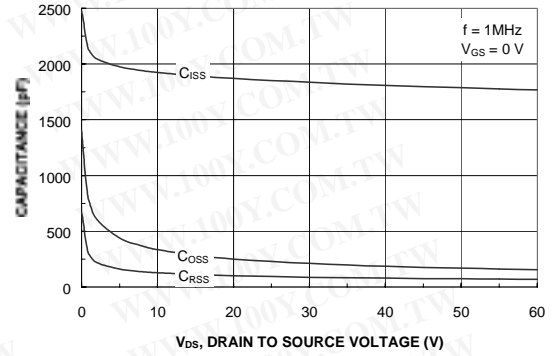


Figure 8. Capacitance Characteristics.

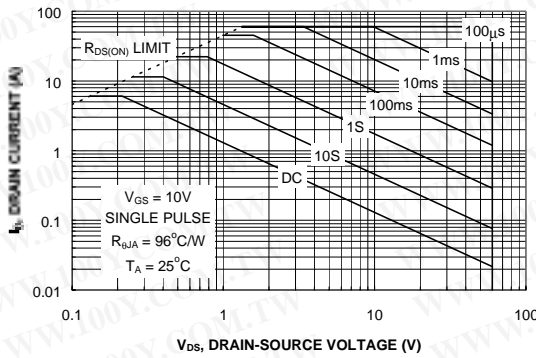


Figure 9. Maximum Safe Operating Area.

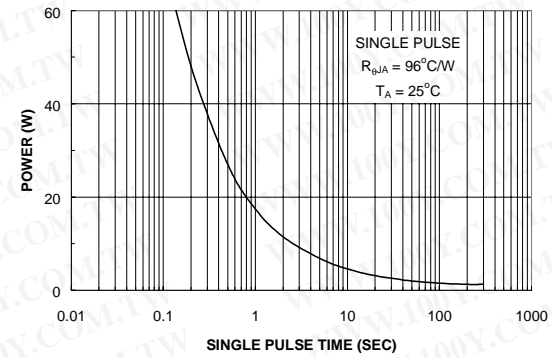


Figure 10. Single Pulse Maximum Power Dissipation.

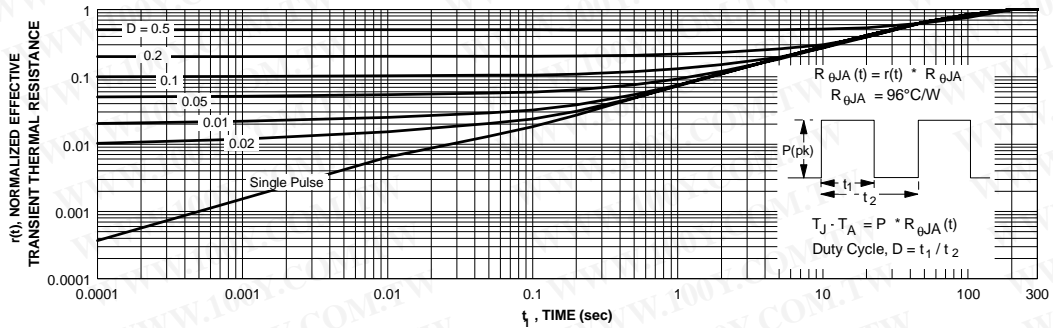


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

## TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACE <sub>x</sub> <sup>TM</sup>	FAST <sup>®</sup>	OPTOLOGIC <sup>TM</sup>	SMART START <sup>TM</sup>	VCX <sup>TM</sup>
Bottomless <sup>TM</sup>	FAST <sub>r</sub> <sup>TM</sup>	OPTOPLANAR <sup>TM</sup>	STAR*POWER <sup>TM</sup>	
CoolFET <sup>TM</sup>	FRFET <sup>TM</sup>	PACMAN <sup>TM</sup>	Stealth <sup>TM</sup>	
CROSSVOLT <sup>TM</sup>	GlobalOptoisolator <sup>TM</sup>	POPT <sup>TM</sup>	SuperSOT <sup>TM</sup> -3	
DenseTrench <sup>TM</sup>	GTO <sup>TM</sup>	Power247 <sup>TM</sup>	SuperSOT <sup>TM</sup> -6	
DOMET <sup>TM</sup>	HiSeC <sup>TM</sup>	PowerTrench <sup>®</sup>	SuperSOT <sup>TM</sup> -8	
EcoSPARK <sup>TM</sup>	ISOPLANAR <sup>TM</sup>	QFET <sup>TM</sup>	SyncFET <sup>TM</sup>	
E <sup>2</sup> CMOS <sup>TM</sup>	LittleFET <sup>TM</sup>	QST <sup>TM</sup>	TinyLogic <sup>TM</sup>	
EnSigna <sup>TM</sup>	MicroFET <sup>TM</sup>	QT Optoelectronics <sup>TM</sup>	TruTranslation <sup>TM</sup>	
FACT <sup>TM</sup>	MicroPak <sup>TM</sup>	Quiet Series <sup>TM</sup>	UHC <sup>TM</sup>	
FACT Quiet Series <sup>TM</sup>	MICROWIRE <sup>TM</sup>	SILENT SWITCHER <sup>®</sup>	UltraFET <sup>®</sup>	

STAR\*POWER is used under license

## DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

## LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

## PRODUCT STATUS DEFINITIONS

### Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

Rev. H4

勝特力材料 886-3-5753170  
勝特力电子(上海) 86-21-34970699  
勝特力电子(深圳) 86-755-83298787  
[Http://www.100y.com.tw](http://www.100y.com.tw)